



40V N-Channel Trench Power MOSFET

General Description

The SJP40ND190 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a wide variety of applications.

Features

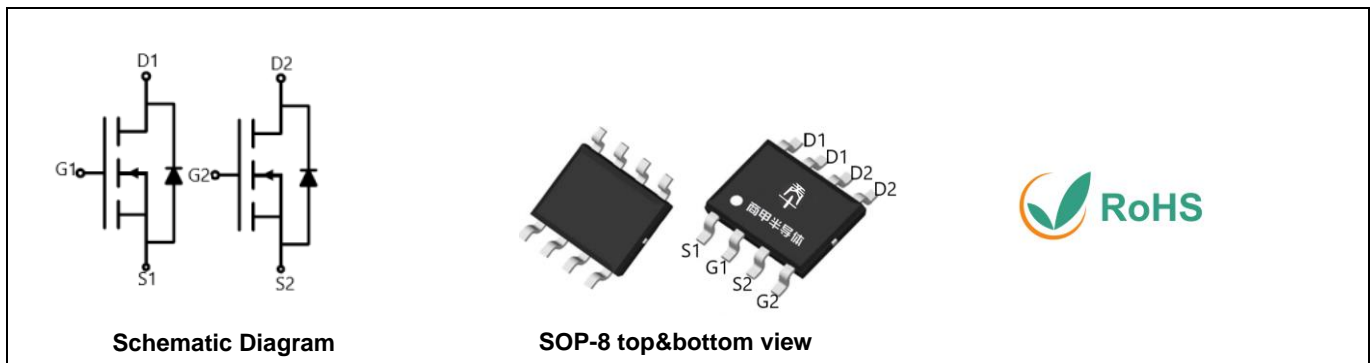
- Low Gate Charge
- High Power and current handing capability
- Lead free product is acquired

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

Key Performance Parametes

Parameter	Value	Unit
V_{DS}	40	V
$R_{DS(ON_TYP)}$	22	m Ω
I_D	5.8	A
Q_G	14.8	nC



Package Marking and Ordering Information

Device/Ordering Code	Marking	Package	Packing	Reel Size	Tape width	Quantity
SJP40ND190	SJP40ND190	SOP-8	Tape	\	\	4000 Pcs

Table 1. Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage ($V_{GS}=0\text{V}$)	40	V
V_{GS}	Gate-Source Voltage ($V_{DS}=0\text{V}$)	± 20	V
I_D	Drain Current-Continuous($T_A=25^{\circ}\text{C}$)	5.8	A
	Drain Current-Continuous($T_A=100^{\circ}\text{C}$)	3.7	A
I_{DM} (pluse)	Drain Current-Continuous@ Current-Pulsed (Note 1)	23.2	A
P_D	Maximum Power Dissipation($T_A=25^{\circ}\text{C}$)	1.6	W
	Maximum Power Dissipation($T_A=100^{\circ}\text{C}$)	0.6	W
E_{AS}	Avalanche energy (Note 2)	64	mJ
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	$^{\circ}\text{C}$

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
$R_{\theta JA}$	Thermal Resistance, Junction-to- Ambient		77	$^{\circ}\text{C}/\text{W}$



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Table 3. Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V I _D =250μA	40			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =40V, V _{GS} =0V T _J =25℃			1	μA
		V _{DS} =40V, V _{GS} =0V T _J =125℃			100	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1		2.5	V
g _{FS}	Forward Transconductance	V _{DS} =10V, I _D =3A		69		S
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =5V, I _D =3A T _J =25℃		22	28.6	mΩ
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =4.5V, I _D =2A T _J =25℃		23.8	31.7	mΩ
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =20V, V _{GS} =0V, f=1.0MHz		726		pF
C _{oss}	Output Capacitance			103		pF
C _{rss}	Reverse Transfer Capacitance			42		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1.0MHz		3.4		Ω
Switching Parameters						
t _{d(on)}	Turn-on Delay Time	V _{GS} =10V, V _{DS} =20V, R _L =6.6Ω, R _{GEN} =3Ω		6.4		nS
t _r	Turn-on Rise Time			2.4		nS
t _{d(off)}	Turn-Off Delay Time			30.8		nS
t _f	Turn-Off Fall Time			3		nS
Q _g	Total Gate Charge	V _{GS} =10V, V _{DS} =20V, I _D =3A		14.8		nC
Q _{gs}	Gate-Source Charge			1.36		nC
Q _{gd}	Gate-Drain Charge			2.84		nC
Source-Drain Diode Characteristics						
I _{SD}	Source-Drain Current (Body Diode)				5.8	A
V _{SD}	Forward on Voltage (Note 3)	V _{GS} =0V, I _S =3A			1.2	V
t _{rr}	Reverse Recovery Time	I _F =3A, dI/dt=100A/μs		12.4		ns
Q _{rr}	Reverse Recovery Charge	I _F =3A, dI/dt=100A/μs		4.3		nC

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature.

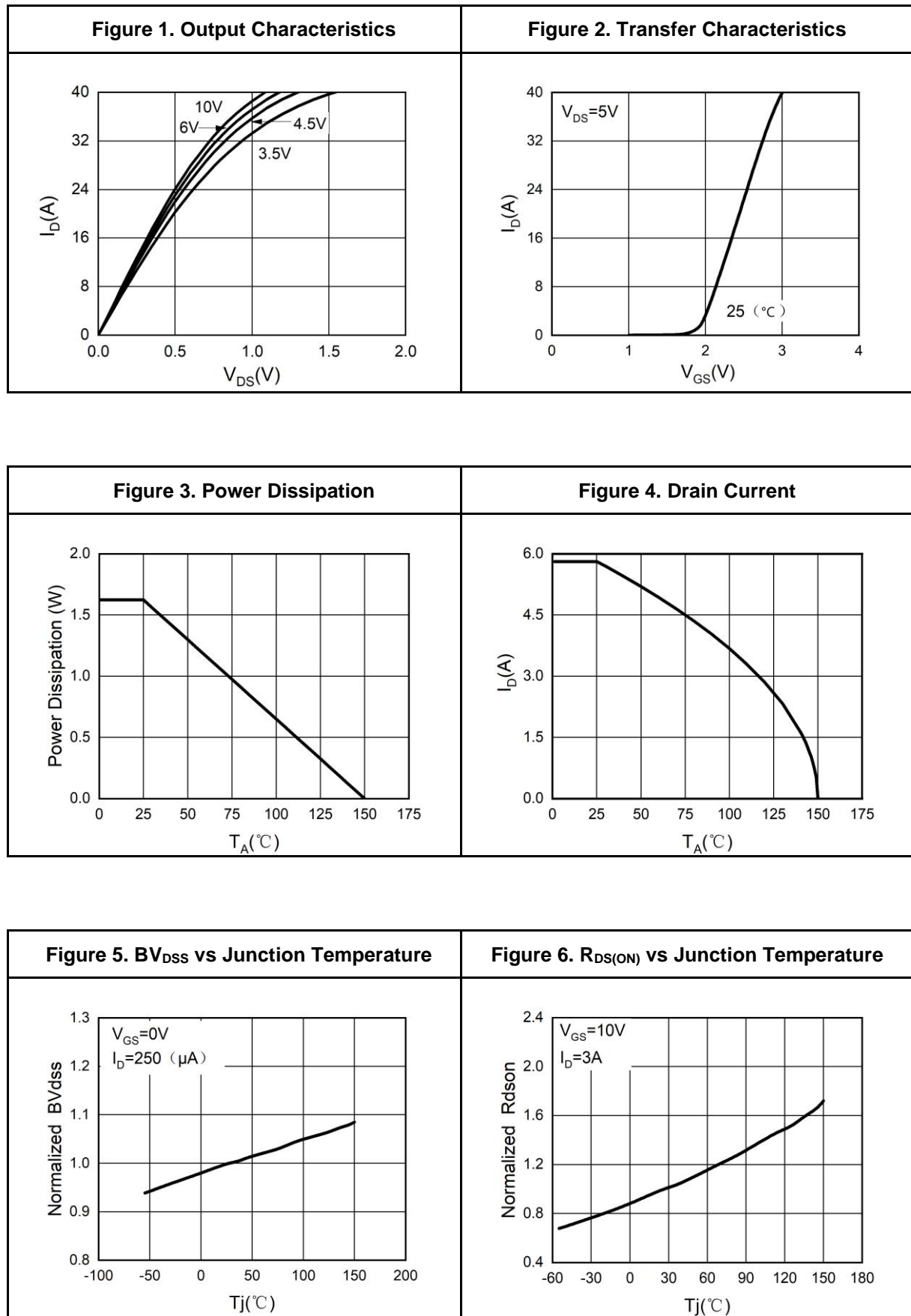
Notes 2.EAS condition: $T_J=25^{\circ}\text{C}, V_{DD}=40V, V_G=10V, R_g=25\Omega, L=0.5\text{mH}$.

Notes 3.Repetitive Rating: Pulse width limited by maximum junction temperature.



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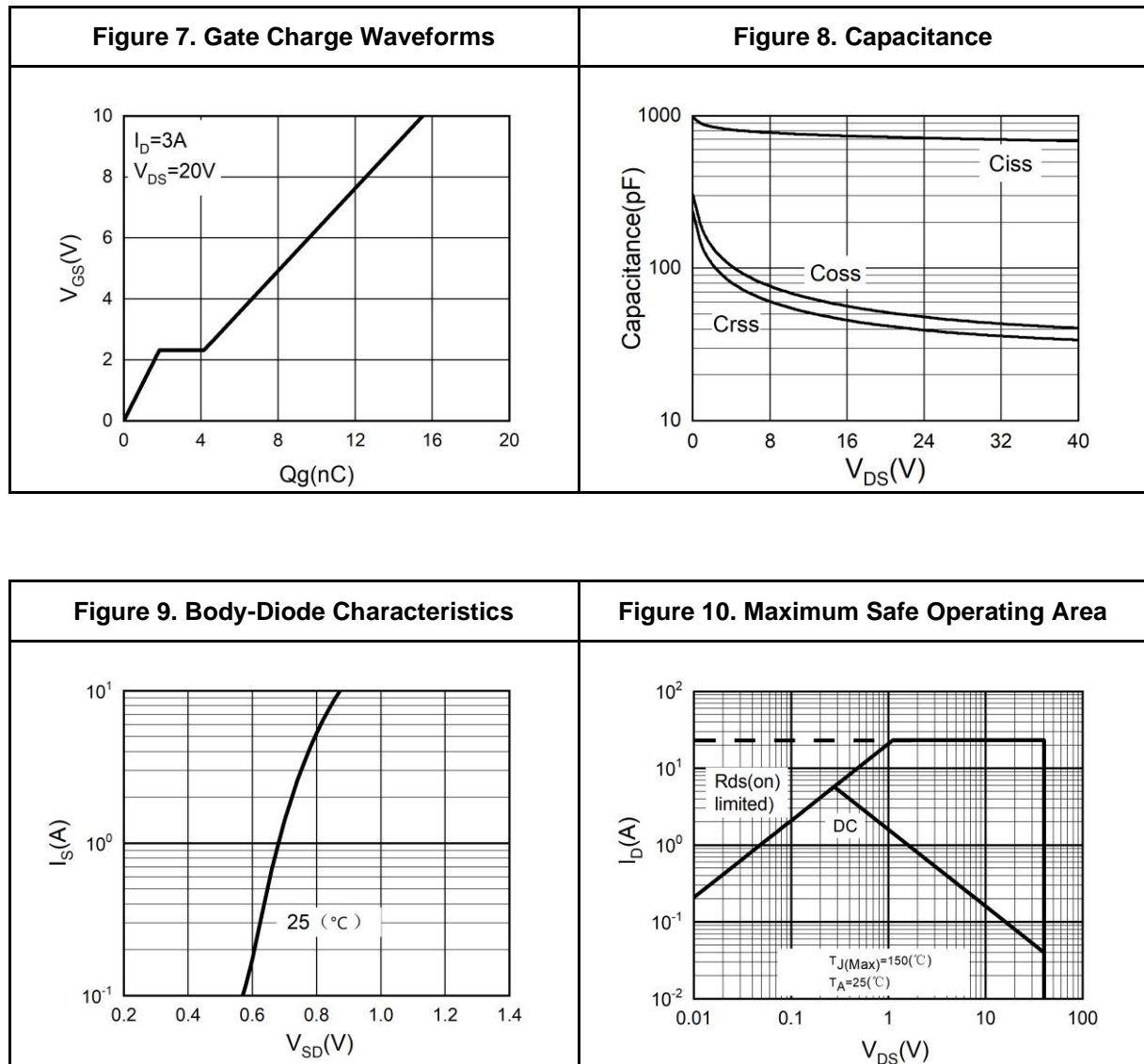
Typical Electrical And Thermal Characteristics (Curves)





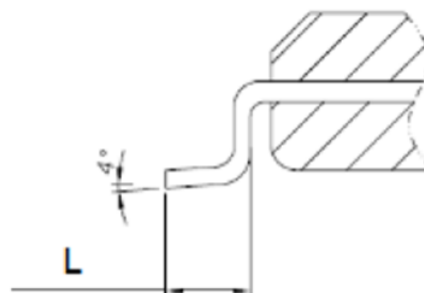
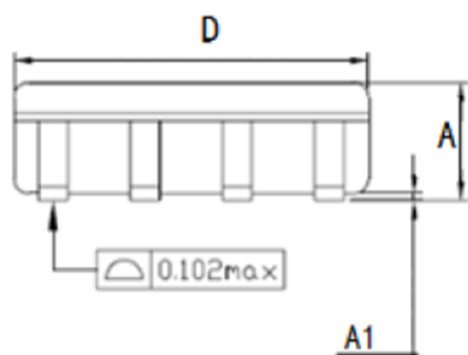
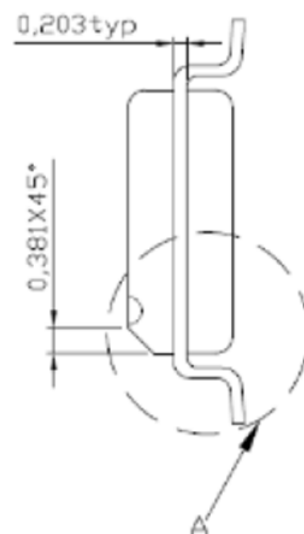
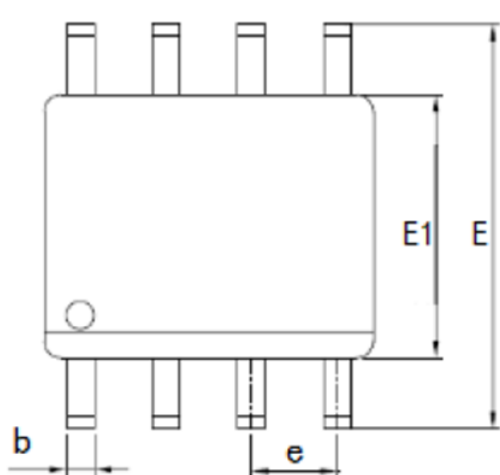
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Typical Electrical And Thermal Characteristics (Curves)





SOP-8 Package Information



A 局部放大

Symbol	Dimensions In Millimeters		
	Min.	Nom.	Max
A	1.35	1.55	1.75
A1	0.1	0.15	0.2
b	0.346	0.406	0.466
D	4.8	4.89	4.98
E	5.75	6.00	6.25
E1	3.81	3.90	3.99
e	1.27TYP		
L	0.406	0.838	1.27



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